

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX16827FT

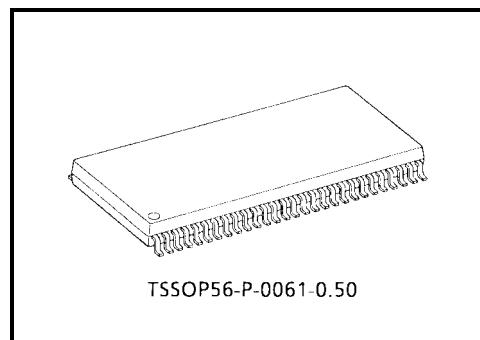
Low-Voltage 20-Bit Bus Buffer with 3.6-V Tolerant Inputs and Outputs

The TC74VCX16827FT is a high-performance CMOS 20-bit bus buffer. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

The TC74VCX16827FT is composed of two 10-bit sections with separate output-enable signals. For either 10-bit buffer section, the two output-enable ($\overline{1OE1}$ and $\overline{1OE2}$ or $\overline{2OE1}$ and $\overline{2OE2}$) inputs must both be low for the corresponding Y outputs to be active. When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

All inputs are equipped with protection circuits against static discharge.

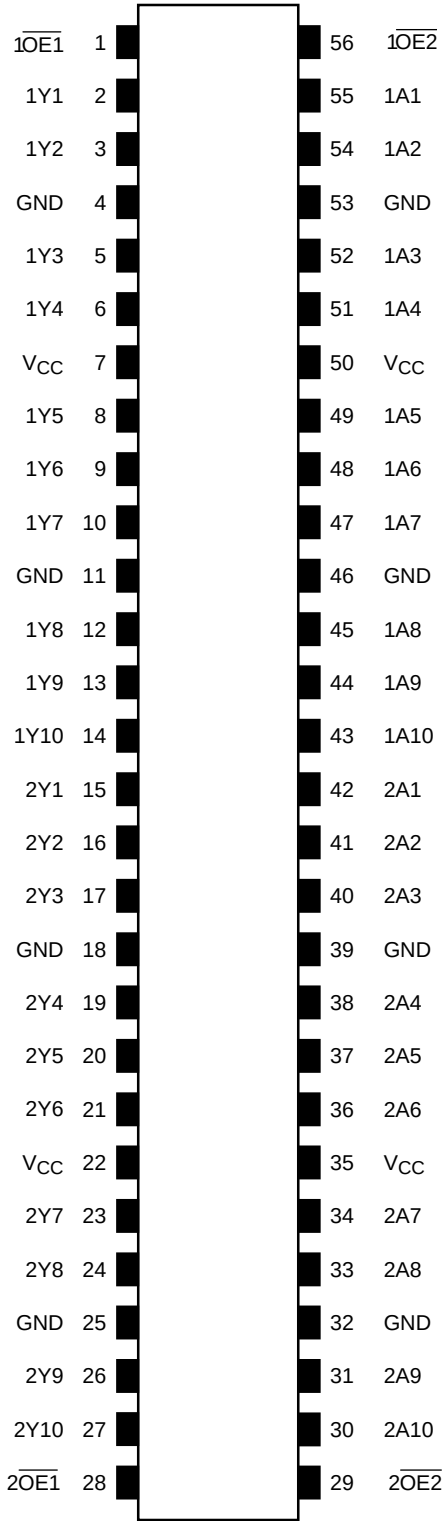


Weight: 0.25 g (typ.)

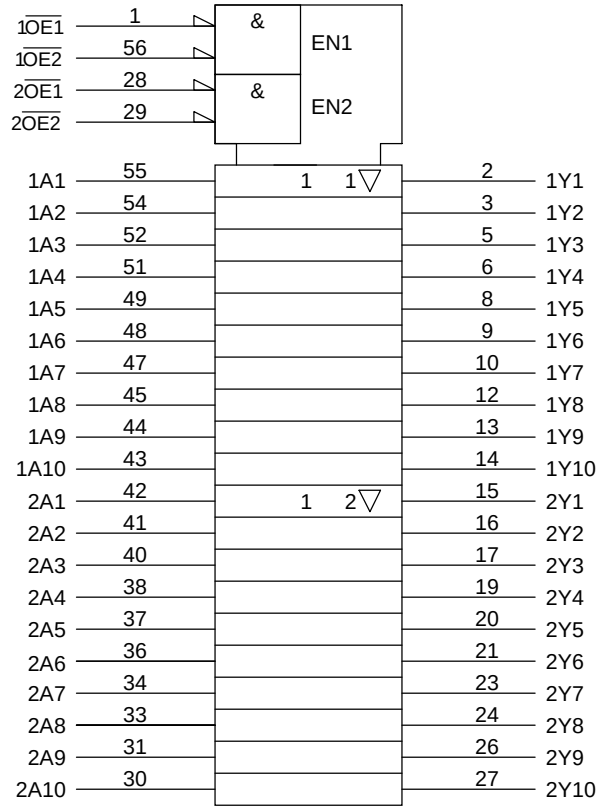
Features

- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation: $t_{pd} = 2.5$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
: $t_{pd} = 3.0$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
: $t_{pd} = 6.0$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 24$ mA (min) ($V_{CC} = 3.0$ V)
: $I_{OH}/I_{OL} = \pm 18$ mA (min) ($V_{CC} = 2.3$ V)
: $I_{OH}/I_{OL} = \pm 6$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
: Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Pin Assignment (top view)



IEC Logic Symbol



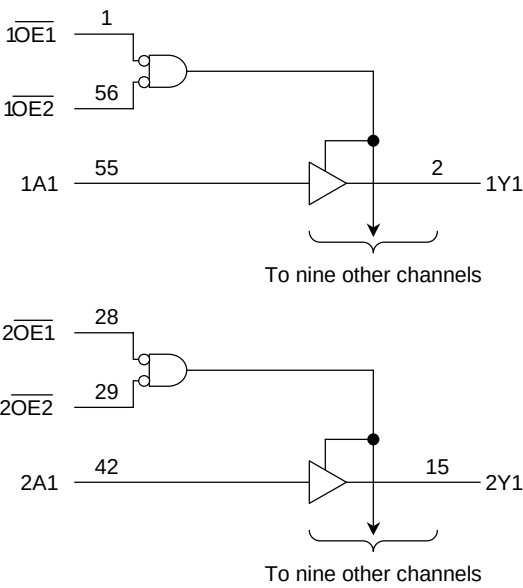
Truth Table (each 10-bit latch)

Input			Output Y
$\overline{OE1}$	$\overline{OE2}$	A	
L	L	L	L
L	L	H	H
H	X	X	Z
X	H	X	Z

X: Don't care

Z: High impedance

System Diagram



Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	−0.5 to 4.6	V
DC input voltage	V_{IN}	−0.5 to 4.6	V
DC output voltage	V_{OUT}	−0.5 to 4.6 (Note 1)	V
		−0.5 to $V_{CC} + 0.5$ (Note 2)	
Input diode current	I_{IK}	−50	mA
Output diode current	I_{OK}	±50 (Note 3)	mA
DC output current	I_{OUT}	±50	mA
Power dissipation	P_D	400	mW
DC V_{CC} /ground current per supply pin	I_{CC}/I_{GND}	±100	mA
Storage temperature	T_{stg}	−65 to 150	°C

Note 1: OFF state

Note 2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 3: $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

Recommended Operating Range

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 4)	
Input voltage	V_{IN}	−0.3 to 3.6	V
Output voltage	V_{OUT}	0 to 3.6 (Note 5)	V
		0 to V_{CC} (Note 6)	
Output current	I_{OH}/I_{OL}	±24 (Note 7)	mA
		±18 (Note 8)	
		±6 (Note 9)	
Operating temperature	T_{opr}	−40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 10)	ns/V

Note 4: Data retention only

Note 5: OFF state

Note 6: High or low state

Note 7: $V_{CC} = 3.0$ to 3.6 V

Note 8: $V_{CC} = 2.3$ to 2.7 V

Note 9: $V_{CC} = 1.8$ V

Note 10: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V

Electrical Characteristics

DC Characteristics ($T_a = -40$ to 85°C , $2.7\text{ V} < V_{CC} \leq 3.6\text{ V}$)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.7 to 3.6	2.0	—	V
	L-level	V _{IL}	—		2.7 to 3.6	—	0.8	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V
				I _{OH} = -12 mA	2.7	2.2	—	
				I _{OH} = -18 mA	3.0	2.4	—	
				I _{OH} = -24 mA	3.0	2.2	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2	
				I _{OL} = 12 mA	2.7	—	0.4	
				I _{OL} = 18 mA	3.0	—	0.4	
				I _{OL} = 24 mA	3.0	—	0.55	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V	2.7 to 3.6	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V	2.7 to 3.6	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V	0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7 to 3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V		2.7 to 3.6	—	±20.0	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V (per input)		2.7 to 3.6	—	750	

DC Characteristics ($T_a = -40$ to 85°C , $2.3\text{ V} \leq V_{CC} \leq 2.7\text{ V}$)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.3 to 2.7	1.6	—	V
	L-level	V _{IL}	—		2.3 to 2.7	—	0.7	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.3	2.0	—	
				I _{OH} = -12 mA	2.3	1.8	—	
				I _{OH} = -18 mA	2.3	1.7	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.3 to 2.7	—	0.2	
				I _{OL} = 12 mA	2.3	—	0.4	
				I _{OL} = 18 mA	2.3	—	0.6	
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V	2.3 to 2.7	—	±5.0	μA	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V	2.3 to 2.7	—	±10.0	μA	
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V	0	—	10.0	μA	
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND	2.3 to 2.7	—	20.0	μA	
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V	2.3 to 2.7	—	±20.0		

DC Characteristics ($T_a = -40$ to 85°C , $1.8\text{ V} \leq V_{CC} < 2.3\text{ V}$)

Characteristics		Symbol	Test Condition			Min	Max	Unit	
			V _{CC} (V)						
Input voltage	H-level	V _{IH}	—		1.8 to 2.3	0.7 × V _{CC}	—	V	
	L-level	V _{IL}	—		1.8 to 2.3	—	0.2 × V _{CC}		
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = −100 μA	1.8	V _{CC} − 0.2	—	V	
				I _{OH} = −6 mA	1.8	1.4	—		
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	1.8	—	0.2		
				I _{OL} = 6 mA	1.8	—	0.3		
Input leakage current		I _{IN}	V _{IN} = 0 to 3.6 V			1.8	—	±5.0	μA
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V			1.8	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V			0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND			1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6 V			1.8	—	±20.0	

AC Characteristics ($T_a = -40$ to 85°C , input: $t_r = t_f = 2.0\text{ ns}$, $C_L = 30\text{ pF}$, $R_L = 500\ \Omega$)

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Propagation delay time		t _{pLH} t _{pHL}	Figure 1, Figure 2		1.8	1.5	6.0	ns
					2.5 ± 0.2	1.0	3.0	
					3.3 ± 0.3	0.8	2.5	
3-state output enable time		t _{pZL} t _{pZH}	Figure 1, Figure 3		1.8	1.5	9.8	ns
					2.5 ± 0.2	1.0	4.9	
					3.3 ± 0.3	0.8	3.8	
3-state output disable time		t _{pLZ} t _{pHZ}	Figure 1, Figure 3		1.8	1.5	7.6	ns
					2.5 ± 0.2	1.0	4.2	
					3.3 ± 0.3	0.8	3.7	
Output to output skew		t _{osLH} t _{osHL}	(Note 11)		1.8	—	0.5	ns
					2.5 ± 0.2	—	0.5	
					3.3 ± 0.3	—	0.5	

For $C_L = 50\text{ pF}$, add approximately 300 ps to the AC maximum specification.

Note 11: Parameter guaranteed by design.

($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

Dynamic Switching Characteristics
(Ta = 25°C, input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	0.8	
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	-0.25	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	-0.6	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	-0.8	
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 12)	1.8	1.5	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 12)	2.5	1.9	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 12)	3.3	2.2	

Note 12: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	C _{OUT}	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note 13)	1.8, 2.5, 3.3	20	pF

 Note 13: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/20 \text{ (per bit)}$$

AC Test Circuit

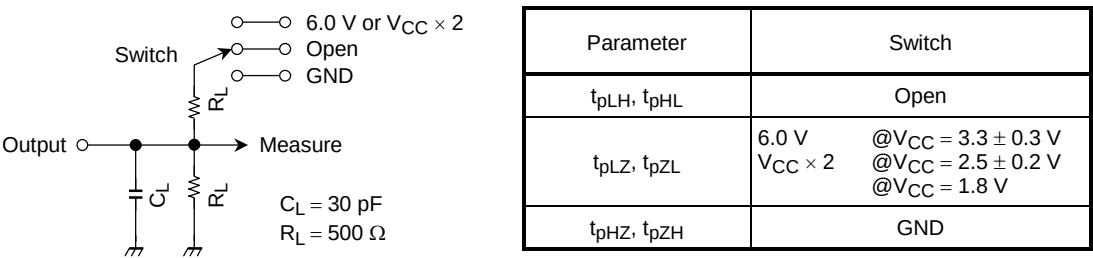


Figure 1

AC Waveform

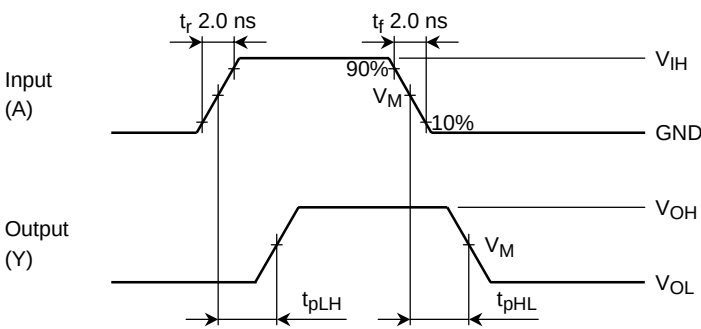


Figure 2 t_{pLH} , t_{pHL}

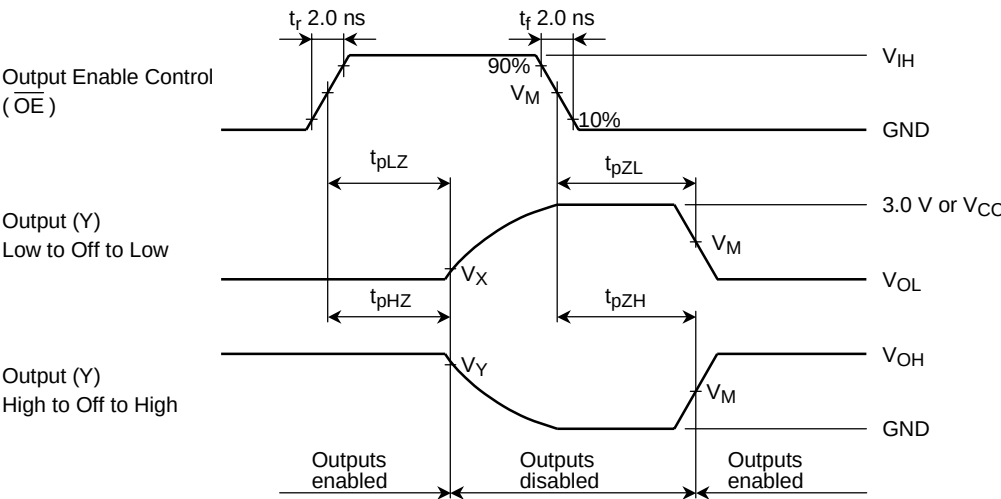


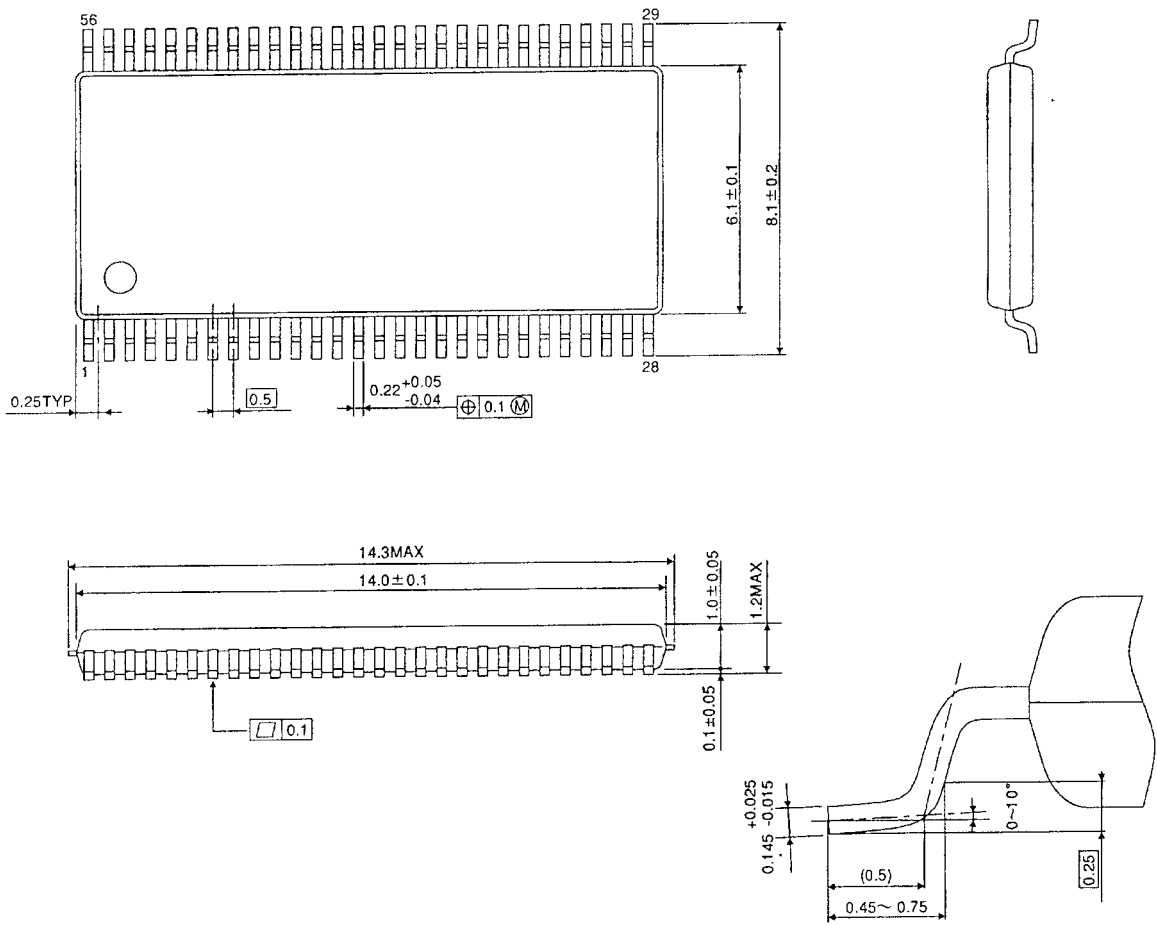
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V _{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V _{IH}	2.7 V	V _{CC}	V _{CC}
V _M	1.5 V	V _{CC} /2	V _{CC} /2
V _X	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V
V _Y	V _{OH} - 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V

Package Dimensions

TSSOP56-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

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